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标题: DIAGNOSTICS OF SEMICONDUCTOR STRUCTURES BY MEANS OF AN APERTURELESS NEAR-FIELD TERAHERTZ MICROSCOPE

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摘要: Carrier density distribution in various semiconductor microstructures is studied by means of a terahertz near-field microscope. The carrier density in the lightly doped p-InAsSbP(Zn) layer in an InAs-based sample is estimated.

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